## **Amendments to the Claims**

Claims 1-96 (Cancelled).

97. (Currently amended) A method for forming a low dielectric constant insulative structure disposed between a pair of conductive lines comprising:

providing the pair of conductive lines over a substrate, the conductive lines each having an upper surface;

forming a mass of a material over the substrate, the mass disposed over and between the pair of conductive lines, the material comprising a mixture of a first material that is substantially vaporizable in an oxidizing atmosphere and a second material that is substantially non-vaporizable in an oxidizing atmosphere;

planarizing the mass to a level about equal to the upper surfaces of the pair of conductive lines;

depositing a layer of insulative material; and

vaporizing at least a portion of the mass disposed between the conductive lines to form the low dielectric constant insulative structure therebetween, the structure comprising at least one void.

98. (Cancelled).

- 99. (Currently amended) The method of Claim <u>97</u> <u>114</u> wherein <del>providing a the</del> <u>first</u> material <del>comprising a mixture</del> comprises <del>providing a mixture of a carbon, and the</del> <u>second <del>comprising material and a comprises</del> silicon oxide <del>material</del>.</u>
- 100. (Currently amended) The method of Claim <u>97</u> <u>114</u> wherein <u>the providing a material comprising a mixture comprises providing a mixture of carbon and SiC<sub>x</sub>, where "x" is a number between about 0.2 and 1.5.</u>
- 101. (Currently amended) The method of Claim <u>97</u> <u>113</u> wherein forming a mass of material comprises forming the mass by plasma decomposition of a hydrocarbon or halogen substituted hydrocarbon.
- 102. (Currently amended) The method of Claim 101 117 wherein forming the mass by plasma decomposition comprises forming a porous carbon mass.
- 103. (Currently amended) The method of Claim <u>97</u> <u>113</u> wherein depositing a layer of an insulative material comprises depositing the layer prior to vaporizing the mass.
- 104. (Currently amended) The method of Claim <u>97</u> <u>113</u> wherein forming a layer of an insulative material comprises forming a silicon oxide layer having a thickness of about 500 Angstroms.

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- 105. (Currently amended) The method of Claim 104 120 wherein forming a silicon oxide layer comprises forming the layer by sputter deposition of silicon dioxide.
- 106. (Currently amended) The method of Claim <u>97</u> <u>113</u> wherein forming a layer of an insulative material comprises forming the layer after vaporizing the mass.
- 107. (Currently amended) The method of Claim <u>97 113</u> wherein forming a mass of material comprises forming the mass of a material comprising about 20% to about 80% SiC<sub>x</sub>, where "x" is a number from about 0.2 to about 1.5.